

FORM PTO 1449 (modified)

U.S. DEPARTMENT OF COMMERCE
PATENT AND TRADEMARK OFFICELIST OF REFERENCES CITED BY APPLICANT(S)
(Use several sheets if necessary)ATTY DOCKET NO.
OGOH:108SERIAL NO.
10/088,264APPLICANT
Shin-Itsu TAKEHASHI et al.FILING DATE
March 18, 2002GROUP
2823

U.S. PATENT DOCUMENTS

*EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
E	6,140,164	10/31/2000	Zhang	438	163	
E	6,127,211	10/03/2000	Hirao et al.	438	158	
E	5,985,701	11/16/1999	Takei et al.	438	154	
E	5,526,304	06/11/1996	Kawamura	365	154	
E	5,476,802	12/19/1995	Yamazaki et al.	437	21	

FOREIGN PATENT DOCUMENTS

	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION NO	YES
E	03-148834	06/25/1991	Japan				Abstract
E	5-55248	03/05/1993	Japan			x	
E	05-082552	04/02/1993	Japan				Abstract
E	06-112222	04/22/1994	Japan				Abstract
E	7-183403	07/21/1995	Japan			x	
E	08-032080	02/02/1996	Japan				Abstract
E	08-148691	06/07/1996	Japan				Abstract
	9-298304	11/18/1997	Japan			x	
E	11-163386	06/18/1999	Japan				Abstract

OTHER DOCUMENT(S) (Including Author, Title, Date, Pertinent Pages, Etc.)

EXAMINER	DATE CONSIDERED 3/10/04

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 608; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION NO	YES
11-168221	06/22/1999	Japan			x	
9-148266	06/06/1997	Japan			x	
10-233511	09/02/1998	Japan				Abstract

OTHER DOCUMENT(S) (Including Author, Title, Date, Pertinent Pages, Etc.)

	"Laser Crystallised Poly-Si Circuits for AMLCDs" Edwards, M.J., et al. ASIA DISPLAY '95, pp. 335-337.
	"New Poly-Si TFT Structure for OFF-Current Reduction" Bae, B.S., et al. SID '98 DIGEST, pp. 25-28.
	AMLCDs and Electronics on Polymer Substrates" Young, N.D., et al. Euro Display '96, pp. 555-558.
	"Gate-Overlapped Lightly Doped Drain Poly-Si Thin-Film Transistors for Large Area-AMLCD" Choi, Kwon-Young, et al. IEEE Transaction on Electronic Devices, Vol. 45, No. 6, June 1998, pp. 1272-1279.
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